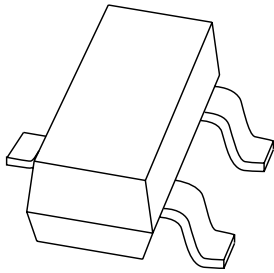


# DATA SHEET



## **BC859; BC860** PNP general purpose transistors

Product data sheet  
Supersedes data of 1999 May 28

2004 Jan 16

# PNP general purpose transistors

# BC859; BC860

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

### APPLICATIONS

- Low noise input stages of audio frequency equipment.

### DESCRIPTION

PNP transistor in a SOT23 plastic package.  
 NPN complements: BC849 and BC850.

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>	TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BC859B	4B*	BC860B	4F*
BC859C	4C*	BC860C	4G*

### Note

- \* = p : Made in Hong Kong.  
 \* = t : Made in Malaysia.  
 \* = W : Made in China.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

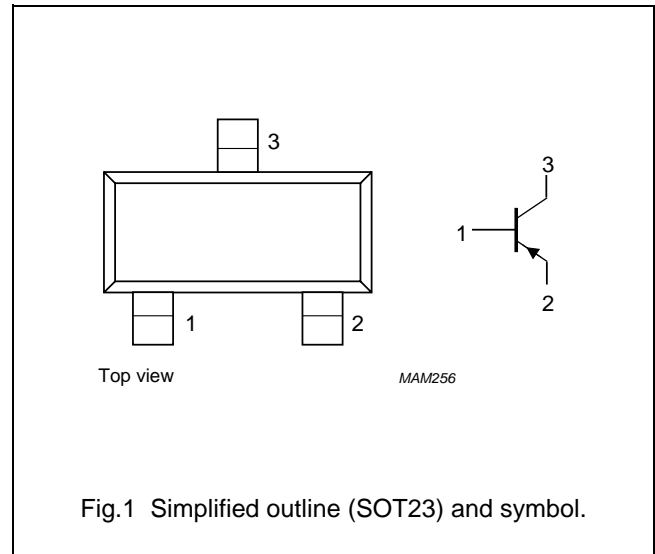


Fig.1 Simplified outline (SOT23) and symbol.

### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BC859B	-	plastic surface mounted package; 3 leads	SOT23
BC859C			
BC860B			
BC860C			

## PNP general purpose transistors

## BC859; BC860

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	–30	V
	BC859			–50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	–30	V
	BC860			–45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–5	V
I <sub>C</sub>	collector current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–200	mA
I <sub>BM</sub>	peak base current		–	–200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

## PNP general purpose transistors

## BC859; BC860

**CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

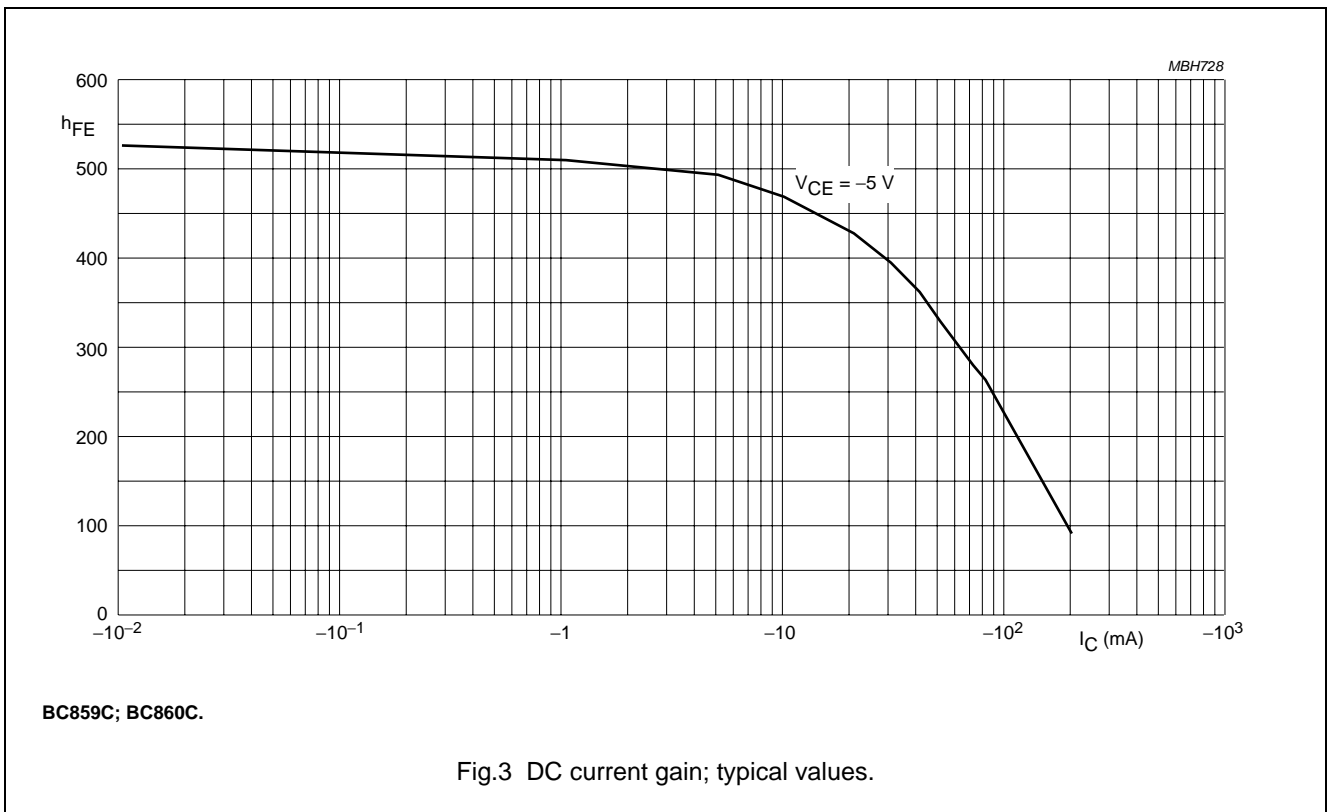
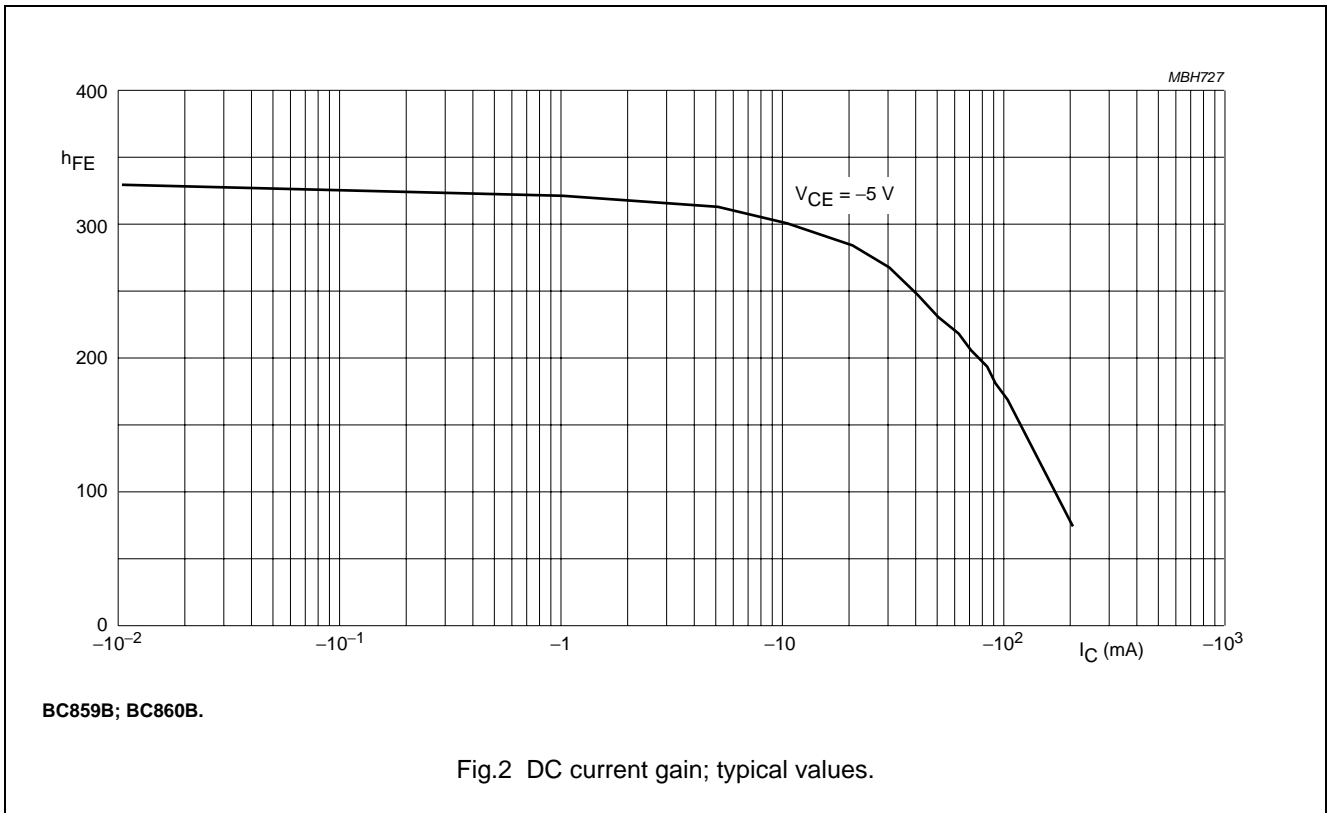
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–1	–15	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$	–	–	–4	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
$h_{FE}$	DC current gain BC859B; BC860B BC859C; BC860C	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ see Figs 2 and 3	220	–	475	
			420	–	800	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–75	–300	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA}$	–	–250	–650	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA};$ note 1	–	–700	–	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–850	–	mV
$V_{BE}$	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–600	–650	–750	mV
		$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–	–	–820	mV
$C_c$	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	4.5	–	pF
$C_e$	emitter capacitance	$I_C = I_c = 0; V_{EB} = -500\text{ mV}; f = 1\text{ MHz}$	–	10	–	pF
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure BC859B; BC860B; BC859C; BC860C	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 30\text{ Hz to }15\text{ kHz}$	–	–	4	dB
	noise figure BC859B; BC860B; BC859C; BC860C	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	4	dB

**Notes**

- $V_{BEsat}$  decreases by about  $-1.7\text{ mV/K}$  with increasing temperature.
- $V_{BE}$  decreases by about  $-2\text{ mV/K}$  with increasing temperature.

PNP general purpose transistors

BC859; BC860



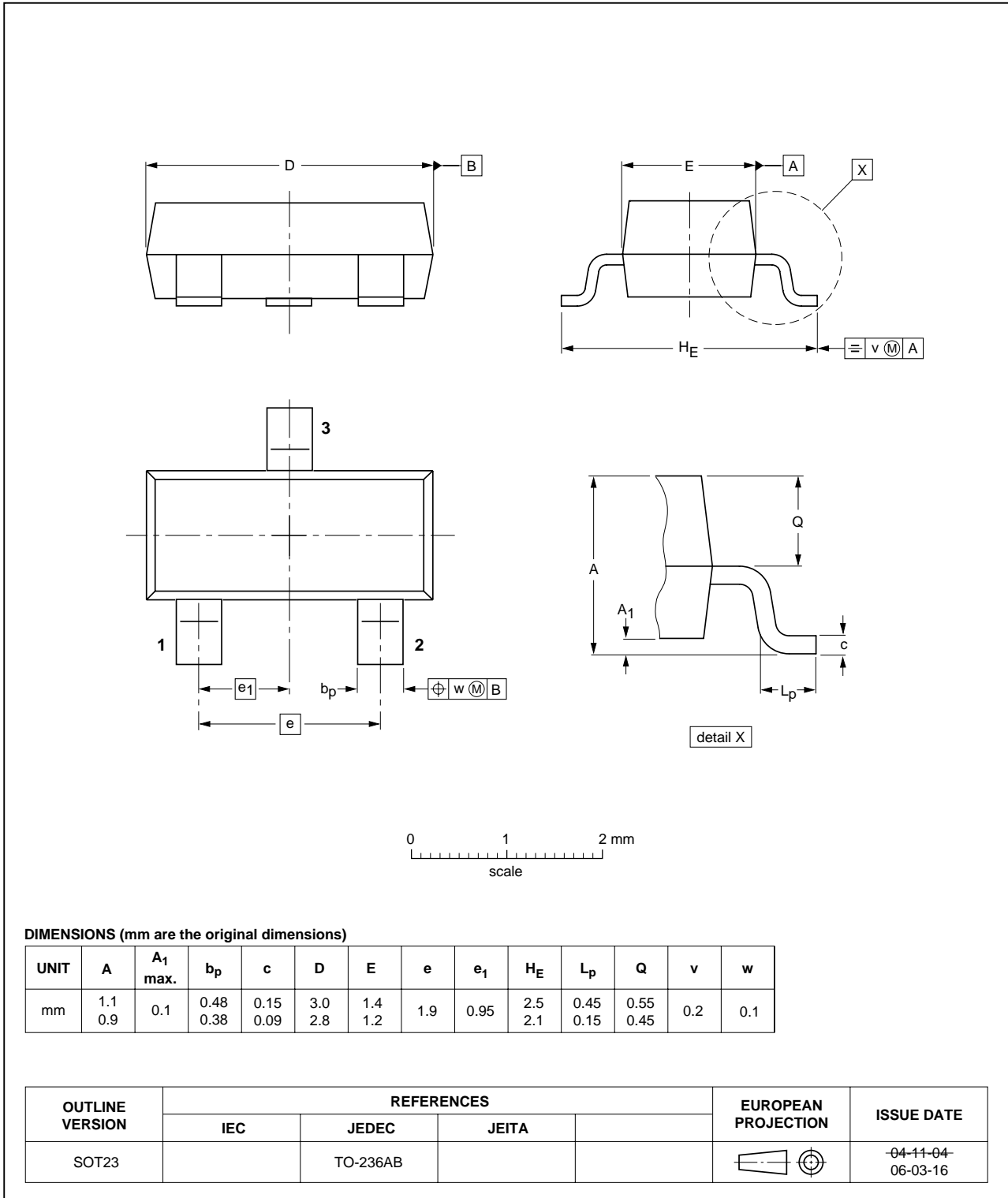
PNP general purpose transistors

BC859; BC860

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



## PNP general purpose transistors

BC859; BC860

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

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